NSR15ADXV6T1, NSR15ADXV6T5

Dual RF Schottky Diode

These diodes are designed for analog and digital applications, including DC based signal detection and mixing applications.

Features

- Low Capacitance (<1.0 pF)
- Low V_F (390 mV Typical @ 1.0 mA)
- Low $V_{F\Delta}$ (1.0 mV Typical @ 1.0 mA)
- These are Pb-Free Devices

Benefits

- Reduced Parasitic Losses
- Accurate Signal Measurement

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Reverse Voltage	V_R	15	V
Forward Current	I _F	30	mA
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C
ESD Rating: Class	Class 1 per Human Body Model		

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

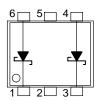
Class A per Machine Model



ON Semiconductor®

http://onsemi.com

RF SCHOTTKY BARRIER DIODES 15 VOLTS, 30 mA



MARKING DIAGRAM



SOT-563 CASE 463A



5R = Specific Device Code D = Date Code

ORDERING INFORMATION

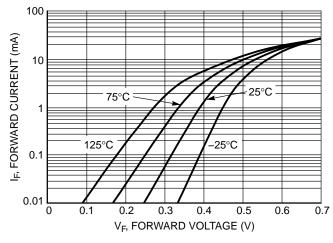
Device	Package	Shipping [†]
NSR15ADXV6T1	SOT-563	4 mm pitch 4000 / Tape & Reel
NSR15ADXV6T5	SOT-563	2 mm pitch 8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSR15ADXV6T1, NSR15ADXV6T5

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Breakdown Voltage (I _R = 10 μA)	V_{BR}	15	20	-	V
Reverse Leakage (V _R = 1.0 V)	I _R	-	2	50	nA
Forward Voltage (I _F = 1.0 mA)	V _{F1}	-	390	415	mV
Forward Voltage (I _F = 10 mA)	V _{F2}	-	530	680	mV
Delta V _F	ΔV_{F}	-	1	15	mV
Capacitance (V _F = 0 V, f = 1.0 MHz)	C _T	-	0.8	1	pF



100 k

(Y) 10 k

125°C

100 k

125°C

100 k

Figure 1. Forward Current versus Forward Voltage at Temperatures

Figure 2. Reverse Current versus Reverse Voltage

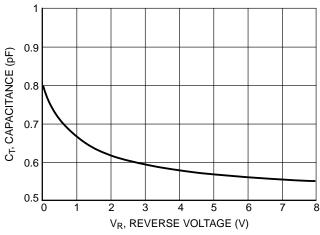


Figure 3. Total Capacitance versus Reverse Voltage

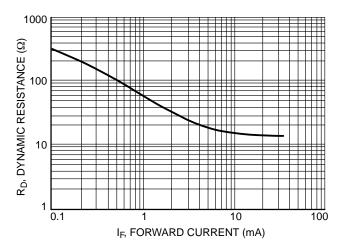


Figure 4. Dynamic Resistance versus Forward Current

NSR15ADXV6T1, NSR15ADXV6T5

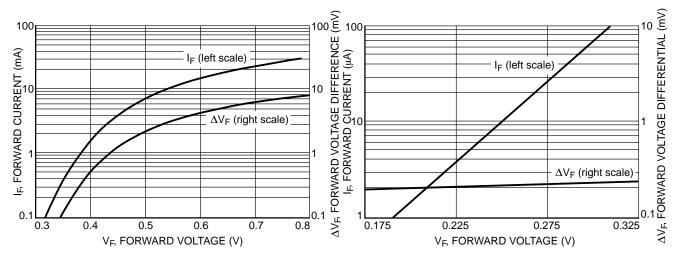


Figure 5. Typical V_F Match at Mixer Bias Levels

Figure 6. Typical V_F Match at Detector Bias Levels

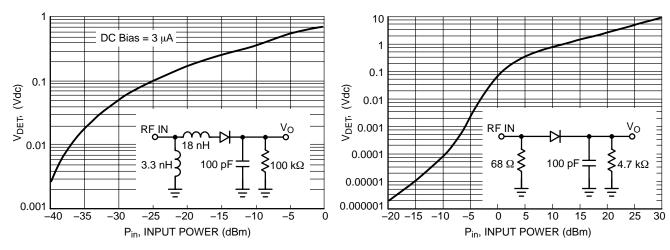


Figure 7. Typical Output Voltage versus Input Power, Small Signal Detector Operating at 850 MHz

Figure 8. Typical Output Voltage versus Input Power, Large Signal Detector Operating at 915 MHz

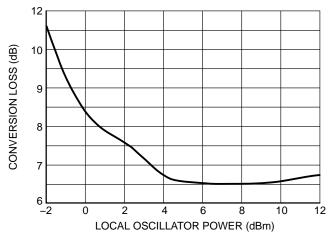


Figure 9. Typical Conversion Loss versus L.O. Drive, 2.0 GHz



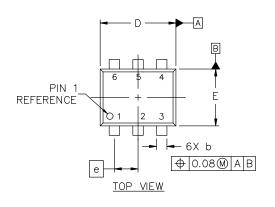


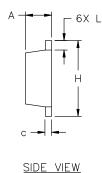
SOT-563-6 1.60x1.20x0.55, 0.50P CASE 463A **ISSUE J**

DATE 15 FEB 2024

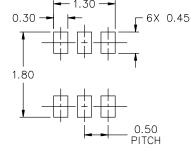
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.





DIM	MILLIMETERS			
ויונע	MIN.	N□M.	MAX.	
Α	0.50	0.55	0.60	
b	0.17	0.22	0.27	
C	0.08	0.13	0.18	
D	1.50	1.60	1.70	
E	1.10	1.20	1.30	
е	0.50 BSC			
Н	1.50	1.60	1.70	
L	0.10	0.20	0.30	



STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHODE 1
2. BASE 1	2. EMITTER 2	2. CATHODE 1
3. COLLECTOR 2	3. BASE 2	3. ANODE/ANODE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHODE 2
5. BASE 2	5. BASE 1	5. CATHODE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. ANODE/ANODE 1

STYLE 6: PIN 1. CATHODE 2. ANODE

3. CATHODE

4. CATHODE 5. CATHODE

CATHODE

RECOMMENDED	MOLINITING	FOOTDRINIT*
KECOMIMENDED	MOONTING	LOO INKINI.

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 7: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 8: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SUURCE 5. DRAIN 6. DRAIN	STYLE 9: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1
--	--	--

STYLE 5

PIN 1. CATHODE

2. CATHODE 3. ANDDE 4. ANDDE 5. CATHODE

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Month Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

PIN 1. CATHODE 1	PIN 1. EMITTER 2
2. N/C	2. BASE 2
3. CATHODE 2	3. COLLECTOR 1
4. ANODE 2	4. EMITTER 1
5. N/C	5. BASE 1
6. AN□DE 1	6. COLLECTOR 2

STYLE 11:

STYLE 4: PIN 1. COLLECTOR

3. BASE 4. EMITTER 5. COLLECTOR

STYLE 10:

2. COLLECTOR

COLLECTOR

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DESCRIPTION: SOT-563-6 1.60x1.20x0.55, 0.50P **PAGE 1 OF 1**

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